

EAST Search History

EAST Search History (Prior Art)

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|------------------------------------------------------------------------------------------|-------------------------------------------------------------------------|------------------|---------|---------------------|
| L35 | 0 | light emitting diodes and nitride and first near4 layer near "10" ("InGaN" or "AlInGaN") | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | OFF | 2010/08/14 18:44 |
| L36 | 7705 | light emitting diodes and nitride and first near4 layer | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | OFF | 2010/08/14 18:44 |
| L37 | 1013 | light emitting diodes and nitride and first near4 layer same indium | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | OFF | 2010/08/14 18:45 |
| L38 | 486 | light emitting diodes and nitride same first near4 layer same indium | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | OFF | 2010/08/14 18:45 |
| L39 | 8 | (light emitting diodes) same nitride same first near4 layer same indium | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | OFF | 2010/08/14 18:46 |
| S3 | 1840 | (257/213,256,257).ccls. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2007/10/26 16:03 |

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| S4 | 2708 | (257/213,256,257;438/167,186;341/136;331/116,117).ccls. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2007/10/26 16:05 |
| S8 | 1 | (photodetector or photodiode or LED) and (intrinsic or undoped) layer and inver\$3 and P-I-N and InGaN | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2007/10/26 16:08 |
| S9 | 170 | (photodetector or photodiode or LED) and (intrinsic or undoped) layer and InGaN | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2007/10/26 16:08 |
| S10 | 106 | (photodetector or photodiode or LED) and (intrinsic or undoped) layer and InGaN and (aluminum or "Al") and (gold or "Au") and sapphire near10 substrate | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2007/10/26 16:10 |
| S11 | 0 | (photodetector or photodiode or LED) and (intrinsic or undoped) layer and InGaN and (aluminum or "Al") and (gold or "Au") and (titanium or "Ti") and ((ITO) or (Ni near2 ITO)) and sapphire near10 substrate and (namometer or "nm") and micrometer and thickness | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2007/10/26 16:14 |
| S14 | 4 | (photodetector or photodiode or LED) and (intrinsic or undoped) layer and InGaN and (aluminum or "Al") and (gold or "Au") and sapphire near10 substrate and (namometer or "nm") and micrometer and thickness | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2007/10/26 16:17 |

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| S19 | 6 | (photodetector or photodiode or LED) and (intrinsic or undoped) layer and InGaN and (aluminum or "Al") and sapphire and substrate and micrometer and thickness | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2007/10/26 16:19 |
| S20 | 10 | (photodetector or photodiode or LED) and (intrinsic or undoped) layer and GaN near10 layer and (aluminum or "Al") and sapphire and substrate and micrometer and thickness | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2007/10/26 16:20 |
| S21 | 351 | (photodetector or photodiode or LED) and GaN near10 layer and (aluminum or "Al") and sapphire and substrate and micrometer and thickness | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2007/10/26 19:34 |
| S22 | 166 | (photodetector or photodiode or LED) and GaN near10 layer and (aluminum or "Al") and sapphire and substrate and nanometer and micrometer and thickness | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2007/10/26 16:20 |
| S25 | 113 | (photodetector or photodiode or LED) and GaN near10 layer and (aluminum or "Al") and sapphire and substrate and nanometer and micrometer and thickness and (gold or "Au") | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2007/10/26 16:47 |
| S26 | 17 | (photodetector or photodiode or LED) and GaN near10 layer and (aluminum or "Al") and sapphire and substrate and nanometer and micrometer and thickness and (gold or "Au") and "ITO" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2007/10/26 16:23 |

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| S27 | 19 | (photodetector or photodiode or LED) and GaN near10 layer and (aluminum or "Al") and sapphire and substrate and nanometer and micrometer and thickness and "ITO" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2007/10/26 16:23 |
| S28 | 6 | US "6258617" B1 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2007/10/26 16:48 |
| S29 | 4 | (photodetector or photodiode or LED) and GaN near10 layer and (aluminum or "Al") and sapphire and substrate and micrometer and thickness transparent | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2007/10/26 19:36 |
| S30 | 20 | (photodetector or photodiode or LED) and GaN near10 layer and (aluminum or "Al") and sapphire and substrate and micrometer and thickness and transparent near10 ohm\$2 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2007/10/26 19:38 |
| S31 | 19 | (photodetector or photodiode or LED) and GaN near10 layer and (aluminum or "Al") and sapphire and substrate and micrometer and thickness and transparent near10 ohm\$2 near5 contact | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2007/10/29 10:39 |
| S32 | 749 | (photodetector or photodiode or LED) and GaN near10 layer and (aluminum or "Al") near5 (titanium or "Ti ") near5 (gold or "Au") and sapphire and substrate | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2007/10/29 10:41 |

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| S33 | 290 | (photodetector or photodiode or LED) and GaN near10 layer and (aluminum or "Al") near5 (titanium or "Ti ") near5 (gold or "Au") near5 electrode and sapphire and substrate | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2007/10/29 10:42 |
| S34 | 122 | (photodetector or photodiode or LED) and GaN near10 layer and (aluminum or "Al") near2 (titanium or "Ti ") near2 (gold or "Au") near2 electrode and sapphire and substrate | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2007/10/29 10:45 |
| S35 | 2 | (photodetector or photodiode or LED) and GaN near10 layer and Al/Ti/Au and (aluminum or "Al") near2 (titanium or "Ti ") near2 (gold or "Au") near2 electrode and sapphire and substrate | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2007/10/29 10:46 |
| S36 | 4 | (photodetector or photodiode or LED) and (intrinsic or undoped) layer and InGaN and (aluminum or "Al") and (gold or "Au") and sapphire and substrate and micrometer and thickness | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2007/10/30 08:56 |
| S37 | 2 | US "20050133809" A1 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 02:24 |
| S39 | 2 | US "20030062529" A1 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 02:25 |
| S40 | 2 | US "20060273327" A1 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 02:26 |

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| S41 | 2 | US "20070096116" A1 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 02:27 |
| S42 | 2 | US "20050224816" A1 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 02:27 |
| S43 | 2 | US "20050285128" A1 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 02:28 |
| S45 | 12 | GaN substrate near10 polish\$3 and substrate near10 etch\$3 and substrate near10 planariz\$3 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 02:30 |
| S46 | 0 | GaN substrate near10 polish\$3 and substrate near10 etched and substrate near10 planarized and quantum well | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 02:31 |
| S47 | 0 | GaN substrate and InGaN near5 n\$1type semiconductor and light\$1emitting and quantum well near5 thickness | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 02:37 |
| S48 | 140 | GaN substrate and InGaN and light\$1emitting and quantum well near5 thickness | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 02:38 |
| S49 | 2 | GaN substrate and InAlGaN near10 (n\$1type) and light\$1emitting and quantum well near5 thickness | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 02:40 |

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| S50 | 25 | GaN substrate and InAlGaN and light\$1emitting and quantum well near5 thickness | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 02:40 |
| S53 | 2 | GaN substrate and InAlGaN and light\$1emitting and aluminum content | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 02:46 |
| S59 | 2 | InAlGaN and light\$1emitting and aluminum near10 percentage | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 02:49 |
| S64 | 2 | GaN substrate and InAlGaN near5 thickness and light\$1emitting and quantum well near5 thickness | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 02:52 |
| S65 | 12 | GaN substrate and InAlGaN near5 semiconduct\$3 and light\$1emitting and quantum well near5 thickness | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 07:05 |
| S66 | 1 | InAlGaN substrate and light\$1emitting and quantum well near5 thickness | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 08:05 |
| S67 | 25 | InAlGaN near5 semiconduct\$3 and light\$1emitting and quantum well near5 thickness | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 08:07 |
| S68 | 7 | AllnGaIn near5 semiconduct\$3 and light\$1emitting and quantum well near5 thickness | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 08:11 |

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| S69 | 2 | All nGa _N substrate and light\$1emitting and quantum well near5 thickness | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 08:17 |
| S70 | 385 | 257/257.ccls. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2008/06/09 08:22 |
| S71 | 0 | (All nGa _N or InAlGa _N) contact and light\$1emitting and quantum well near5 thickness | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 08:25 |
| S72 | 0 | (All nGa _N or InAlGa _N) contact and light\$1emitting and quantum well | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 08:25 |
| S73 | 2 | (All nGa _N or InAlGa _N) contact and light\$1emitting | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 08:25 |
| S74 | 73 | (All nGa _N or InAlGa _N) near5 n\$1type and light\$1emitting | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 08:28 |
| S75 | 1 | US 2004/0041156 A1 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 08:45 |
| S76 | 3 | US "20040041156" A1 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 08:46 |

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| S77 | 2 | US "20020088985" A1 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 08:48 |
| S78 | 2 | US "20020079506" A1 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 08:50 |
| S79 | 1412 | (Al near5 In near5 Ga near5 N) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 08:58 |
| S80 | 0 | (Al near5 In near5 Ga near5 N) substrate and light\$1emitting and quantum well near5 thickness | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 08:59 |
| S81 | 25 | (Al near3 In near3 Ga near3 N) and light\$1emitting and quantum well near5 thickness | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 09:00 |
| S82 | 25 | (Al near3 In near3 Ga near3 N) and light\$1emitting and quantum well near5 thickness | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 09:00 |
| S83 | 42 | (Al near5 In near5 Ga near5 N) and light\$1emitting and quantum well near5 thickness | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 09:03 |
| S84 | 0 | GaN substrate (Al near5 In near5 Ga near5 N) and light\$1emitting and quantum well near5 thickness | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 09:04 |

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| S85 | 17 | GaN substrate and (Al near5 In near5 Ga near5 N) and light\$1emitting and quantum well near5 thickness | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/09 09:04 |
| S86 | 6 | US "6462358" B1 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/19 16:58 |
| S87 | 2 | US "20070296077" A1 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2008/06/19 17:13 |
| S88 | 12 | GaN substrate and InAlGaN near5 semiconduct\$3 and light\$1emitting and quantum well near5 thickness | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2009/01/21 10:15 |
| S89 | 1 | InAlGaN substrate and light\$1emitting and quantum well near5 thickness | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2009/01/21 10:16 |
| S90 | 220 | (Kinoshita near2 Yoshitaka) or (KAMEI near2 HIDENORI) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2009/01/21 10:20 |
| S91 | 18 | ((Kinoshita near2 Yoshitaka) or (KAMEI near2 HIDENORI)) and quantum well | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2009/01/21 10:20 |
| S92 | 591 | ((Hasegawa near2 Yoshiaki) or (Yokogawa near2 Toshiya) or (Ishibashi near2 Akihiko)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2009/01/21 11:00 |

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| S93 | 71 | ((Hasegawa near2 Yoshiaki) or (Yokogawa near2 Toshiya) or (Ishibashi near2 Akihiko)) and nitride and light\$1emitting | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2009/01/21 11:01 |
| S94 | 27 | (Al near5 In near5 Ga near5 N) and light\$1emitting and quantum well near5 thickness and diodes | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | OFF | 2009/01/21 13:52 |
| S95 | 0 | GaN substrate and In adj2 GaN near3 clad\$4 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2009/06/19 01:01 |
| S96 | 180 | GaN substrate and (InGaN or InAlGaN or AlInGaN) near3 clad\$4 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2009/06/19 01:02 |
| S97 | 159 | diode and GaN substrate and (InGaN or InAlGaN or AlInGaN) near3 clad\$4 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2009/06/19 01:02 |
| S98 | 153 | light emitting near5 diode and GaN substrate and (InGaN or InAlGaN or AlInGaN) near3 clad\$4 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2009/06/19 01:02 |
| S99 | 0 | light emitting near5 diode and GaN substrate and (InGaN or InAlGaN or AlInGaN) near2clad\$4 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2009/06/19 01:03 |
| S100 | 52 | light emitting near5 diode and GaN substrate and (InGaN or InAlGaN or AlInGaN) near2 clad\$4 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2009/06/19 01:04 |

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| S101 | 8 | light emitting near5 diode and GaN substrate and (InGa _N or InAlGa _N or AlInGa _N) clad\$4 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2009/06/19 01:13 |
| S102 | 9 | GaN substrate and (InGa _N or InAlGa _N or AlInGa _N) clad\$4 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2009/06/19 13:16 |
| S103 | 0 | "III-V" near3 Nitride near3 substrate and (InGa _N or InAlGa _N or AlInGa _N) clad\$4 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2009/06/19 13:22 |
| S104 | 25 | Nitride near3 substrate and (InGa _N or InAlGa _N or AlInGa _N) clad\$4 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2009/06/19 13:23 |
| S105 | 23 | GaN substrate and (InGa _N or InAlGa _N or AlInGa _N or indium) near10 reduce near3 strain | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2010/02/27 21:43 |
| S106 | 3 | US "20040207323" A1 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | ADJ | ON | 2010/02/27 23:17 |

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